



## General Description

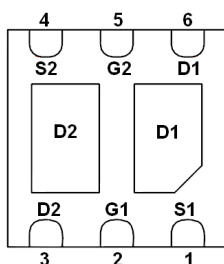
AFP2913W, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

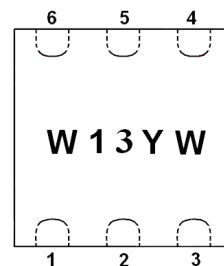
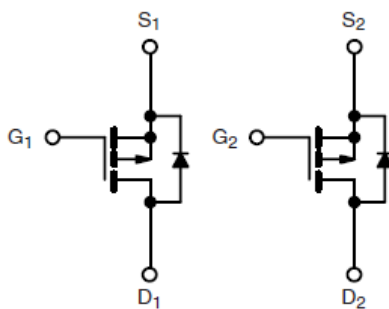
## Features

- $I_D = -4.5A, R_{DS(ON)} = 120m\Omega @ V_{GS} = -10V$
- $I_D = -3.8A, R_{DS(ON)} = 155m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN2X2-6L package design

## Pin Description ( DFN2X2-6L )



BOTTOM VIEW



TOP VIEW

## Application

- Load Switch
- Portable Equipment
- Battery Powered System

## Pin Define

Pin	Symbol	Description
1	S1	Source1
2	G1	Gate1
3	D2	Drain2
4	S2	Source2
5	G2	Gate2
6	D1	Drain1

## Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP2913WFN226RG	W13YW	DFN2X2-6L	Tape & Reel	4000 EA

※ W13 parts code

※ Y year code

※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )

※ AFP2913WFN226RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



### Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

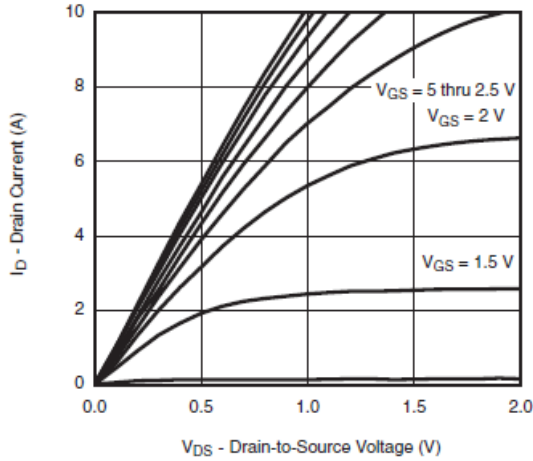
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-25	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-4.5
		T <sub>A</sub> =70°C	-3.8
Pulsed Drain Current	I <sub>DM</sub>	-12	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	6.5
		T <sub>A</sub> =70°C	4.2
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

### Electrical Characteristics

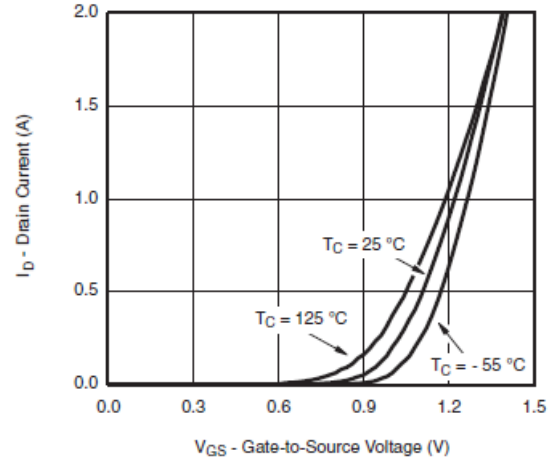
(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-25			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.0		-2.5	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	uA
		V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-30	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> =-4.5V	-8			A
		V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> =-2.5V	-3			
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.5A		108	120	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.8A		142	155	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-2.8A		6.5		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.25A, V <sub>GS</sub> =0V		-0.75	-1.3	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V I <sub>D</sub> ≡-3.5A		5	10	nC
Gate-Source Charge	Q <sub>gs</sub>			0.85		
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V f=1MHz		375		pF
Output Capacitance	C <sub>oss</sub>			80		
Reverse Transfer Capacitance	C <sub>rss</sub>			60		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, R <sub>L</sub> =2.85Ω I <sub>D</sub> ≡-3.5A, V <sub>GEN</sub> =-4.5V R <sub>G</sub> =1Ω		15	25	ns
	t <sub>r</sub>			36	60	
Turn-Off Time	t <sub>d(off)</sub>			25	50	
	t <sub>f</sub>			15	25	

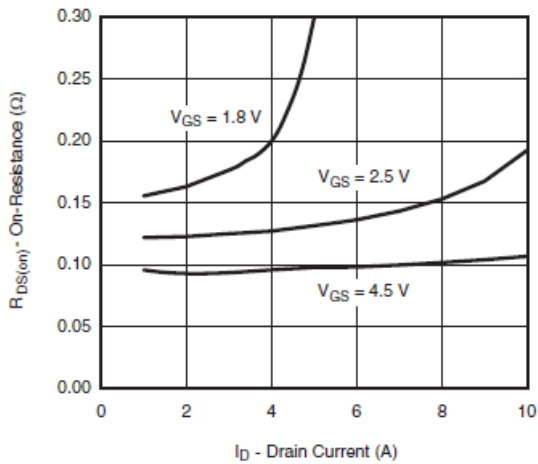
### Typical Characteristics



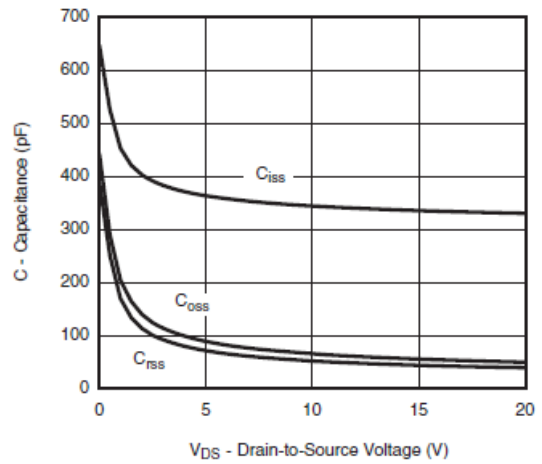
Output Characteristics



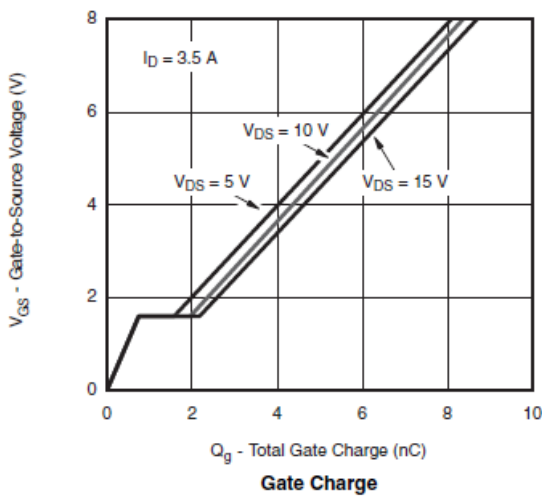
Transfer Characteristics



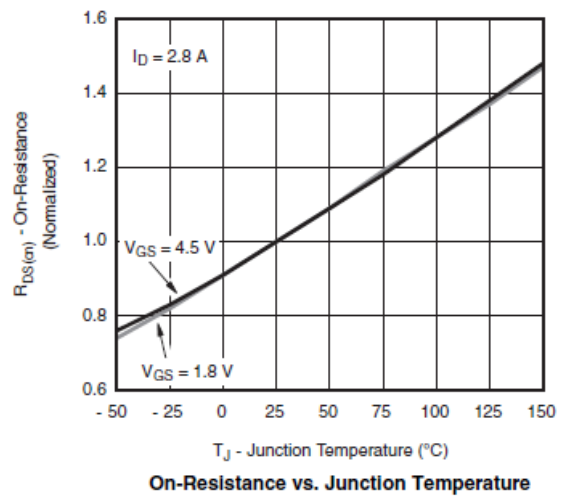
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

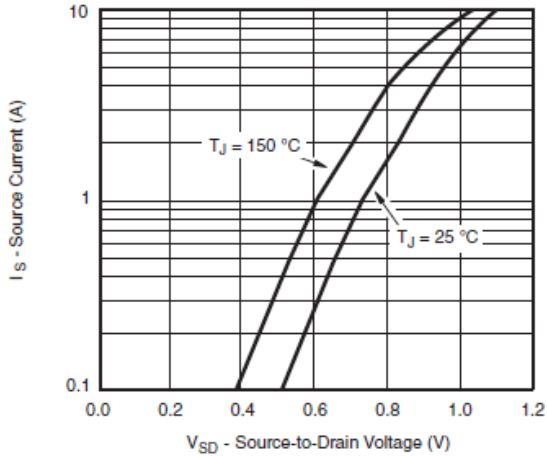


Gate Charge

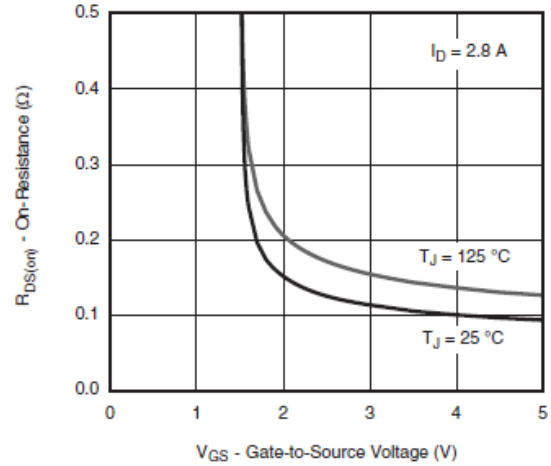


On-Resistance vs. Junction Temperature

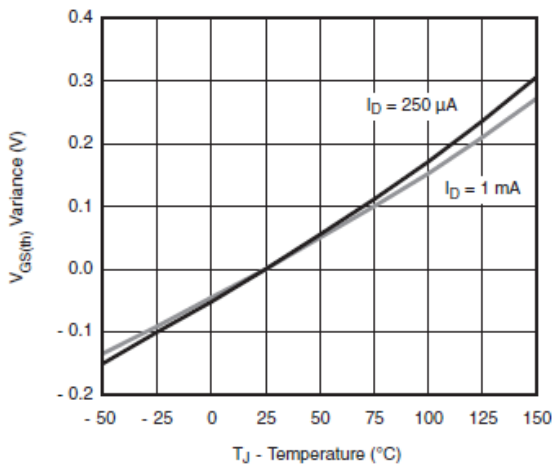
## Typical Characteristics



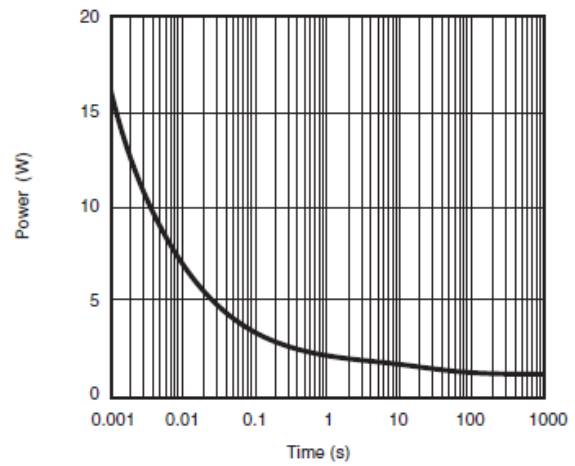
Source-Drain Diode Forward Voltage



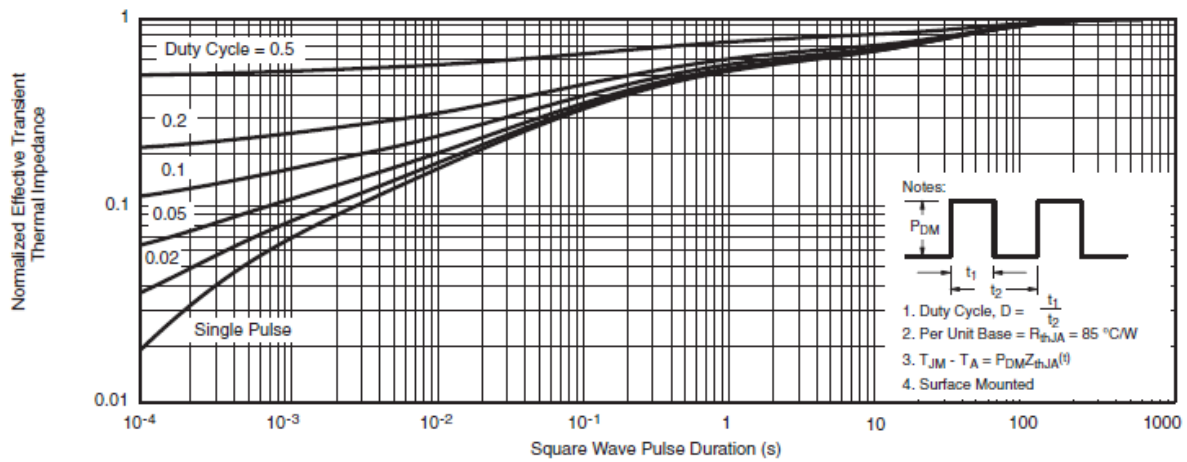
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

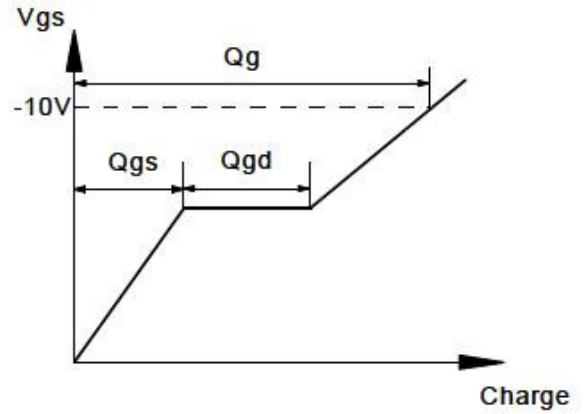
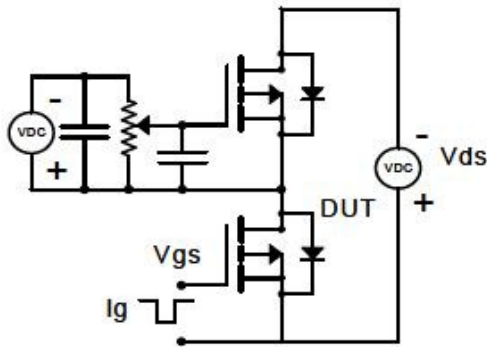


Normalized Thermal Transient Impedance, Junction-to-Ambient

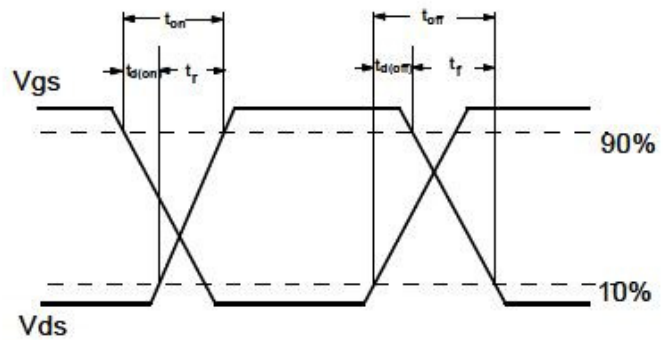
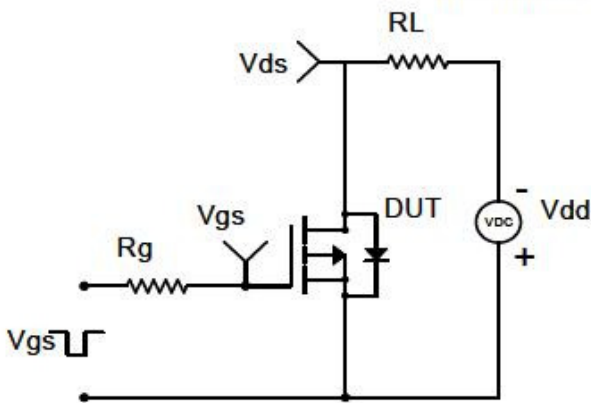
## Typical Characteristics



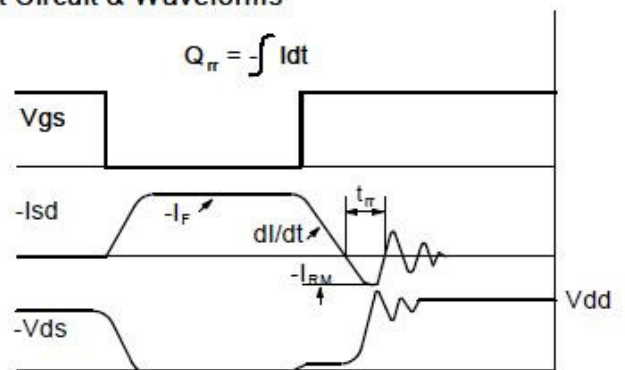
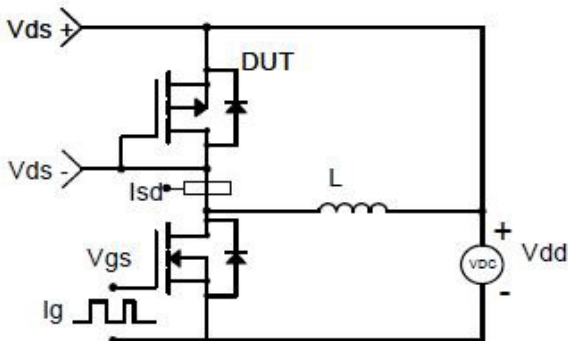
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

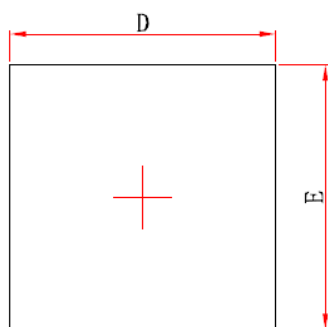


Diode Recovery Test Circuit & Waveforms

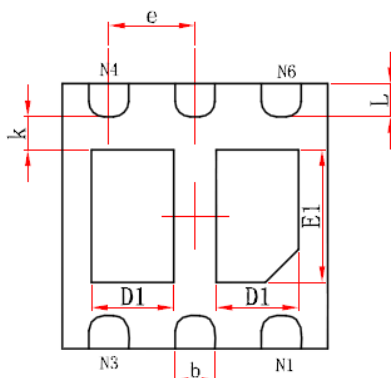




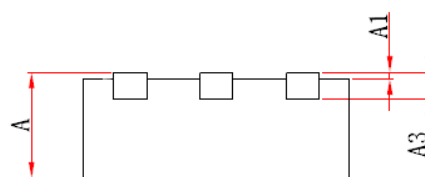
**Package Information ( DFN2X2-6L )**



**Top View**



**Bottom View**



**Side View**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.520	0.720	0.020	0.028
E1	0.900	1.100	0.035	0.043
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

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